

2SA844

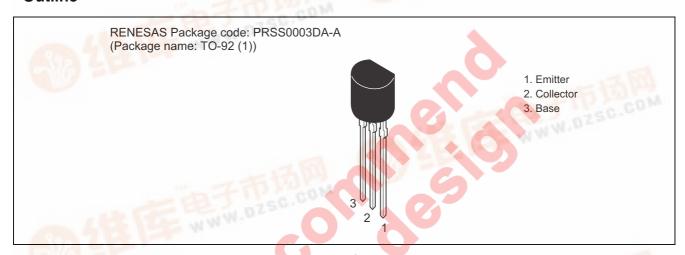
Silicon PNP Epitaxial

REJ03G0630-0200 (Previous ADE-208-320) Rev.2.00 Aug.10.2005

Application

Low frequency amplifier

Outline



Absolute Maximum Ratings

 $(Ta = 25^{\circ}C)$

Item	Symbol	Ratings	Unit
Collector to base voltage	V _{CBO}	-55	V
Collector to emitter voltage	V _{CEO}	- 55	V
Emitter to base voltage	V_{EBO}	-5	V
Collector current	Ic	-100	mA
Emitter current	I _E	100	mA
Collector power dissipation	Pc	300	mW
Junction temperature	Tj	150	°C
Storage temperature	Tstg	-55 to +150	°C

Electrical Characteristics

 $(Ta = 25^{\circ}C)$

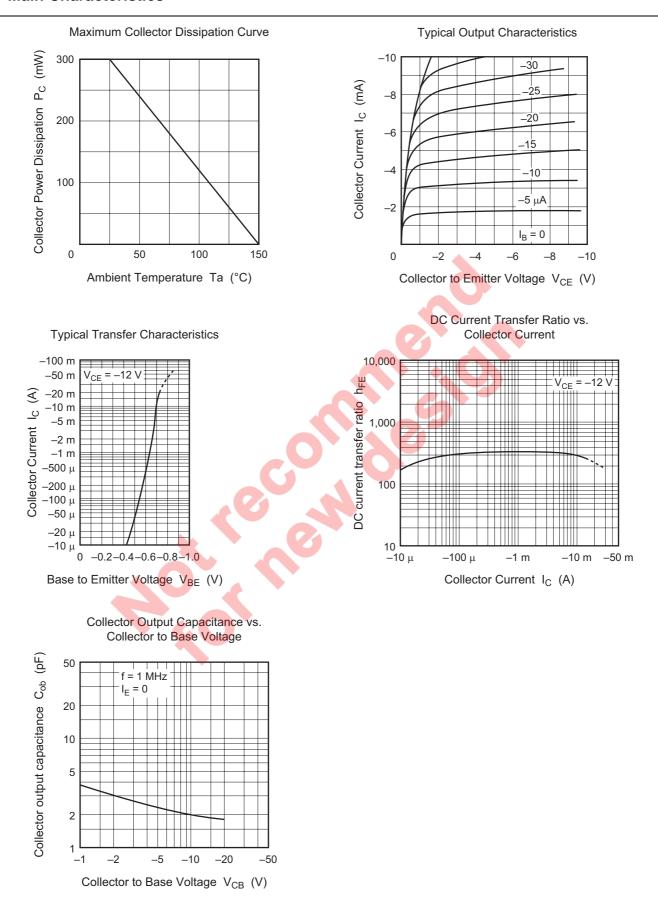
Item	Symbol	Min	Тур	Max	Unit	Test conditions
Collector to base breakdown voltage	$V_{(BR)CBO}$	-55	_	_	V	$I_C = -10 \mu A, I_E = 0$
Collector to emitter breakdown voltage	$V_{(BR)CEO}$	-55	_	_	V	$I_C = -1 \text{ mA}, R_{BE} = \infty$
Emitter to base breakdown voltage	$V_{(BR)EBO}$	- 5	_	_	V	$I_E = -10 \ \mu A, \ I_C = 0$
Collector cutoff current	I _{CBO}	_	_	-100	nA	$V_{CB} = -18 \text{ V}, I_E = 0$
Emitter cutoff current	I _{EBO}	_	_	-50	nA	$V_{EB} = -2 \text{ V}, I_C = 0$
DC current transfer ratio	h _{FE} *1	160	_	500		$V_{CE} = -12 \text{ V}, I_{C} = -2 \text{ mA}$
Collector to emitter saturation voltage	$V_{CE(sat)}$	_	-0.1	-0.5	V	$I_C = -10 \text{ mA}, I_B = -1 \text{ mA}$
Base to emitter voltage	V_{BE}	_	-0.66	-0.75	V	$V_{CE} = -12 \text{ V}, I_{C} = -2 \text{ mA}$
Gain bandwidth product	f _T	_	200	_	MHz	$V_{CE} = -12 \text{ V}, I_{E} = -2 \text{ mA}$
Collector output capacitance	Cob	_	2.0	_	pF	$V_{CB} = -10 \text{ V}, I_E = 0, f = 1 \text{ MHz}$

Note: 1. The 2SA844 is grouped by h_{FE} as follows.

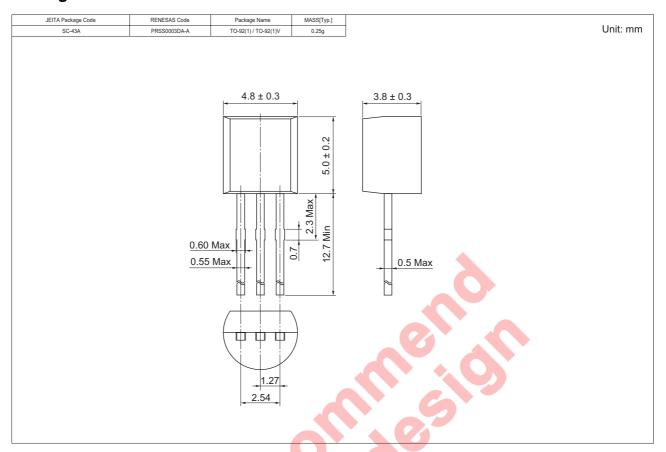
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D

160 to 320 250 to 500	C	ן ט	
	160 to 320	250 to 500	
			V *O).
			0, 70
40,100			10 1
40,41			
201			

Main Characteristics



Package Dimensions



Ordering Information

Part Name	Quantity	Shipping Container
2SA844CTZ	2500	Hold Box, Radial Taping
2SA844DTZ		

Note: For some grades, production may be terminated. Please contact the Renesas sales office to check the state of production before ordering the product.

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